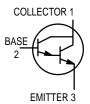
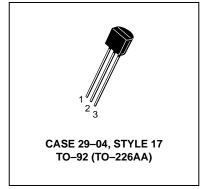
Darlington Transistors NPN Silicon

BC517





MAXIMUM RATINGS

| Rating | Symbol | Value | Unit | |
|--|-----------------------------------|-------------|----------------|--|
| Collector-Emitter Voltage | VCES | 30 | Vdc | |
| Collector-Base Voltage | VCB | 40 | Vdc | |
| Emitter-Base Voltage | VEB | 10 | Vdc | |
| Collector Current — Continuous | IC | 1.0 | Adc | |
| Total Power Dissipation @ T _A = 25°C Derate above 25°C | PD | 625 12 | mW mW/°C | |
| Total Power Dissipation @ T _C = 25°C Derate above 25°C | PD | 1.5 12 | Watts mW/°C | |
| Operating and Storage Junction Temperature Range | T _J , T _{stg} | -55 to +150 | °C | |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|---|-----------------|------|------|
| Thermal Resistance, Junction to Ambient | $R_{	heta JA}$ | 200 | °C/W |
| Thermal Resistance, Junction to Case | $R_{\theta JC}$ | 83.3 | °C/W |

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Тур | Max | Unit |
|--|------------------|-----|-----|-----|------|
| OFF CHARACTERISTICS | | | | | |
| Collector-Emitter Breakdown Voltage (I _C = 2.0 mAdc, V _{BE} = 0) | V(BR)CES | 30 | _ | _ | Vdc |
| Collector-Base Breakdown Voltage (I _C = 10 μAdc, I _E = 0) | V(BR)CBO | 40 | _ | _ | Vdc |
| Emitter-Base Breakdown Voltage (IE = 100 nAdc, IC = 0) | V(BR)EBO | 10 | _ | _ | Vdc |
| Collector Cutoff Current (VCE = 30 Vdc) | ICES | _ | _ | 500 | nAdc |
| Collector Cutoff Current (V _{CB} = 30 Vdc, I _E = 0) | СВО | _ | _ | 100 | nAdc |
| Emitter Cutoff Current (VEB = 10 Vdc, IC = 0) | I _{EBO} | _ | _ | 100 | nAdc |

BC517

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

| Characteristic | Symbol | Min | Тур | Max | Unit |
|---|-----------------|--------|-----|-----|------|
| ON CHARACTERISTICS(1) | | | | | |
| DC Current Gain (IC = 20 mAdc, VCE = 2.0 Vdc) | h _{FE} | 30,000 | _ | _ | _ |
| Collector-Emitter Saturation Voltage (IC = 100 mAdc, IB = 0.1 mAdc) | VCE(sat) | _ | _ | 1.0 | Vdc |
| Base-Emitter On Voltage (IC = 10 mAdc, VCE = 5.0 Vdc) | VBE(on) | _ | _ | 1.4 | Vdc |
| SMALL-SIGNAL CHARACTERISTICS | • | • | | | |
| Current-Gain — Bandwidth Product ⁽²⁾ (IC = 10 mAdc, V _{CE} = 5.0 Vdc, f = 100 MHz) | fŢ | _ | 200 | _ | MHz |

^{1.} Pulse Test: Pulse Width \leq 2.0%.

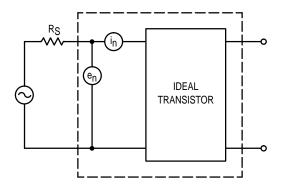
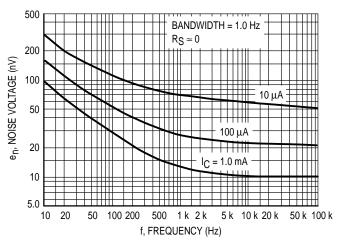


Figure 1. Transistor Noise Model

^{2.} $f_T = |h_{fe}| \bullet f_{test}$

NOISE CHARACTERISTICS

 $(VCE = 5.0 \text{ Vdc}, T_A = 25^{\circ}C)$



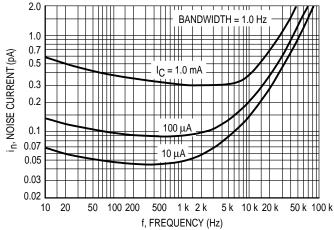
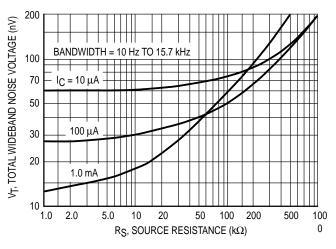


Figure 2. Noise Voltage

Figure 3. Noise Current



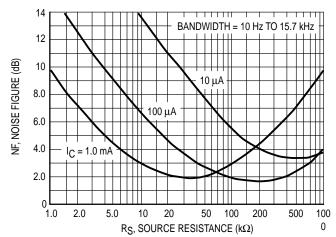


Figure 4. Total Wideband Noise Voltage

Figure 5. Wideband Noise Figure

SMALL-SIGNAL CHARACTERISTICS

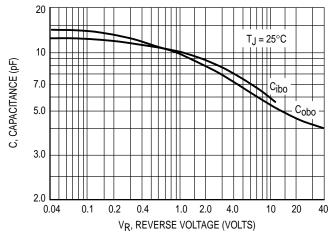


Figure 6. Capacitance

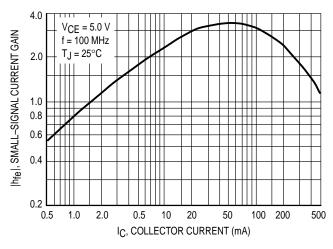


Figure 7. High Frequency Current Gain

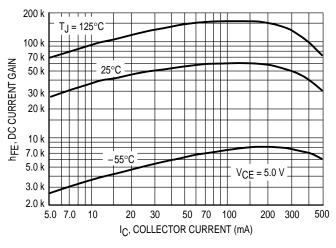


Figure 8. DC Current Gain

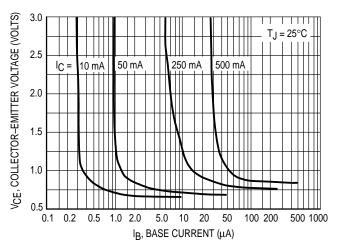


Figure 9. Collector Saturation Region

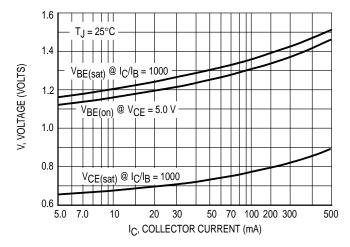


Figure 10. "On" Voltages

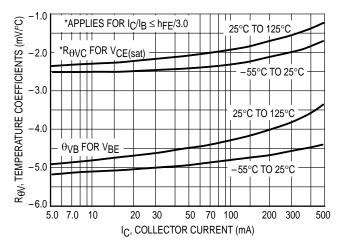


Figure 11. Temperature Coefficients

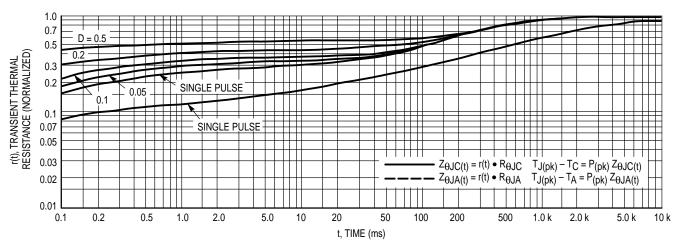
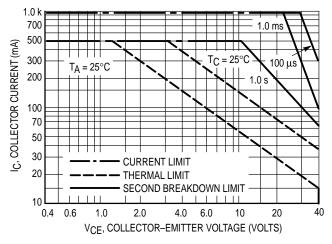


Figure 12. Thermal Response



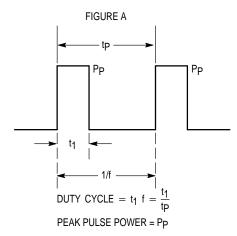
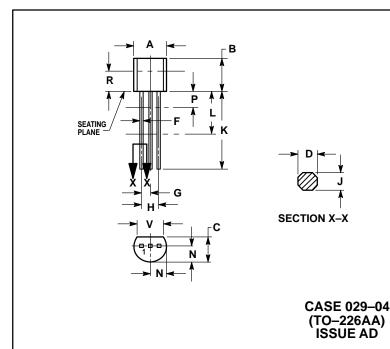


Figure 13. Active Region Safe Operating Area

Design Note: Use of Transient Thermal Resistance Data

PACKAGE DIMENSIONS



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K
 MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

| | INCHES | | MILLIN | IETERS |
|-----|--------|-------|--------|--------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.175 | 0.205 | 4.45 | 5.20 |
| В | 0.170 | 0.210 | 4.32 | 5.33 |
| С | 0.125 | 0.165 | 3.18 | 4.19 |
| D | 0.016 | 0.022 | 0.41 | 0.55 |
| F | 0.016 | 0.019 | 0.41 | 0.48 |
| G | 0.045 | 0.055 | 1.15 | 1.39 |
| Н | 0.095 | 0.105 | 2.42 | 2.66 |
| J | 0.015 | 0.020 | 0.39 | 0.50 |
| K | 0.500 | | 12.70 | |
| L | 0.250 | | 6.35 | |
| N | 0.080 | 0.105 | 2.04 | 2.66 |
| Р | | 0.100 | | 2.54 |
| R | 0.115 | | 2.93 | |
| v | 0.135 | | 3 43 | |

STYLE 17: PIN 1. COLLECTOR 2. BASE 3. EMITTER

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